

TRADEMARK ASSIGNMENT

Electronic Version v1.1
 Stylesheet Version v1.1

SUBMISSION TYPE:	NEW ASSIGNMENT		
NATURE OF CONVEYANCE:	SECURITY INTEREST		
CONVEYING PARTY DATA			
Name	Formerly	Execution Date	Entity Type
NITRONEX CORPORATION		04/26/2010	CORPORATION: DELAWARE
RECEIVING PARTY DATA			
Name:	SILICON VALLEY BANK		
Street Address:	3003 TASMAN DRIVE		
City:	SANTA CLARA		
State/Country:	CALIFORNIA		
Postal Code:	95054-1191		
Entity Type:	CHARTERED BANK: CALIFORNIA		
PROPERTY NUMBERS Total: 6			
Property Type	Number	Word Mark	
Registration Number:	3091510	SIGANTIC	
Registration Number:	2967342	NITRONEX	
Registration Number:	2952096	SIGANTIC	
Registration Number:	2949681	N	
Registration Number:	2925552	NITRONEX	
Serial Number:	77447606	IT'S WATTS IN THE PACKAGE	
CORRESPONDENCE DATA			
Fax Number:	(404)962-6736		
	<i>Correspondence will be sent via US Mail when the fax attempt is unsuccessful.</i>		
Phone:	(404) 885-3038		
Email:	michael.brignati@troutmansanders.com		
Correspondent Name:	MICHAEL J. BRIGNATI, PH.D.		
Address Line 1:	TROUTMAN SANDERS LLP		
Address Line 2:	600 PEACHTREE STREET, N.E.		
Address Line 4:	ATLANTA, GEORGIA 30308-2216		

OP \$165.00 3091510

ATTORNEY DOCKET NUMBER:	220763.000571
NAME OF SUBMITTER:	Michael J. Brignati, Ph.D.
Signature:	/Michael J. Brignati 60,890/
Date:	05/04/2010

Total Attachments: 9

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INTELLECTUAL PROPERTY SECURITY AGREEMENT

THIS INTELLECTUAL PROPERTY SECURITY AGREEMENT is entered into as of the Effective Date by and between SILICON VALLEY BANK, a California corporation ("**Bank**") and NITRONEX CORPORATION, a Delaware corporation ("**Grantor**").

RECITALS

A. Bank has agreed to make certain advances of money and to extend certain financial accommodation to Grantor (the "**Loans**") in the amounts and manner set forth in that certain Loan and Security Agreement by and between Bank and Grantor dated the Effective Date (as the same may be amended, modified or supplemented from time to time, the "**Loan Agreement**"; capitalized terms used herein are used as defined in the Loan Agreement). Bank is willing to make the Loans to Grantor, but only upon the condition, among others, that Grantor shall grant to Bank a security interest in certain Copyrights, Trademarks, Patents, and Mask Works (as each term is described below) to secure the obligations of Grantor under the Loan Agreement.

B. Pursuant to the terms of the Loan Agreement, Grantor has granted to Bank a security interest in all of Grantor's right, title and interest, whether presently existing or hereafter acquired, in, to and under all of the Collateral.

NOW, THEREFORE, for good and valuable consideration, receipt of which is hereby acknowledged, and intending to be legally bound, as collateral security for the prompt and complete payment when due of its obligations under the Loan Agreement, Grantor hereby represents, warrants, covenants and agrees as follows:

AGREEMENT

To secure its obligations under the Loan Agreement, Grantor grants and pledges to Bank a security interest in all of Grantor's right, title and interest in, to and under its intellectual property (all of which shall collectively be called the "**Intellectual Property Collateral**"), including, without limitation, the following:

(a) Any and all copyright rights, copyright applications, copyright registrations and like protections in each work or authorship and derivative work thereof, whether published or unpublished and whether or not the same also constitutes a trade secret, now or hereafter existing, created, acquired or held, including without limitation those set forth on Exhibit A attached hereto (collectively, the "**Copyrights**");

(b) Any and all trade secrets, and any and all intellectual property rights in computer software and computer software products now or hereafter existing, created, acquired or held;

(c) Any and all design rights that may be available to Grantor now or hereafter existing, created, acquired or held;

(d) All patents, patent applications and like protections including, without limitation, improvements, divisions, continuations, renewals, reissues, extensions and

continuations-in-part of the same, including without limitation the patents and patent applications set forth on Exhibit B attached hereto (collectively, the “**Patents**”);

(e) Any trademark and servicemark rights, whether registered or not, applications to register and registrations of the same and like protections, and the entire goodwill of the business of Grantor connected with and symbolized by such trademarks, including without limitation those set forth on Exhibit C attached hereto (collectively, the “**Trademarks**”);

(f) All mask works or similar rights available for the protection of semiconductor chips, now owned or hereafter acquired, including, without limitation those set forth on Exhibit D attached hereto (collectively, the “**Mask Works**”);

(g) Any and all claims for damages by way of past, present and future infringements of any of the rights included above, with the right, but not the obligation, to sue for and collect such damages for said use or infringement of the intellectual property rights identified above;

(h) All licenses or other rights to use any of the Copyrights, Patents, Trademarks, or Mask Works and all license fees and royalties arising from such use to the extent permitted by such license or rights;

(i) All amendments, extensions, renewals and extensions of any of the Copyrights, Trademarks, Patents, or Mask Works; and

(j) All proceeds and products of the foregoing, including without limitation all payments under insurance or any indemnity or warranty payable in respect of any of the foregoing.

This security interest is granted in conjunction with the security interest granted to Bank under the Loan Agreement. The rights and remedies of Bank with respect to the security interest granted hereby are in addition to those set forth in the Loan Agreement and the other Loan Documents, and those which are now or hereafter available to Bank as a matter of law or equity. Each right, power and remedy of Bank provided for herein or in the Loan Agreement or any of the Loan Documents, or now or hereafter existing at law or in equity shall be cumulative and concurrent and shall be in addition to every right, power or remedy provided for herein and the exercise by Bank of any one or more of the rights, powers or remedies provided for in this Intellectual Property Security Agreement, the Loan Agreement or any of the other Loan Documents, or now or hereafter existing at law or in equity, shall not preclude the simultaneous or later exercise by any person, including Bank, of any or all other rights, powers or remedies.

[Signature Page Follows.]

IN WITNESS WHEREOF, the parties have caused this Intellectual Property Security Agreement to be duly executed by its officers thereunto duly authorized as of the first date written above.

Address of Grantor:

2305 Presidential Drive
Durham, North Carolina 27703

Attn: Jim DeVivo

GRANTOR:

NITRONEX CORPORATION

By: Charles E. Shalvo

Name: Charles E. Shalvo
Title: President and CEO

Address of Bank:

3003 Tasman Drive
Santa Clara, CA 95054-1191

Attn: _____

BANK:

SILICON VALLEY BANK

By: Cory Waters

Name: Cory Waters
Title: VP/Relationship Mgr.

EXHIBIT A

Copyrights

<u>Description</u>	Registration/ Application <u>Number</u>	Registration/ Application <u>Date</u>
None		

EXHIBIT B

Patents

<u>Title</u>	<u>Patent/Patent Application Number (Publication Number)</u>	<u>Issue/Filing Date</u>
GALLIUM NITRIDE MATERIAL TRANSISTORS AND METHODS ASSOCIATED WITH THE SAME	7,569,871	08/04/2009
GALLIUM NITRIDE MATERIAL DEVICES INCLUDING CONDUCTIVE REGIONS AND METHODS ASSOCIATED WITH THE SAME	7,566,913	07/28/2009
GALLIUM NITRIDE MATERIAL STRUCTURES INCLUDING SUBSTRATES AND METHODS ASSOCIATED WITH THE SAME	7,365,374	04/29/2008
SEMICONDUCTOR DEVICE-BASED SENSORS	7,361,946	04/22/2008
GALLIUM NITRIDE MATERIAL TRANSISTORS AND METHODS ASSOCIATED WITH THE SAME	7,352,016	04/01/2008
GALLIUM NITRIDE MATERIALS AND METHODS ASSOCIATED WITH THE SAME	7,352,015	04/01/2008
GALLIUM NITRIDE MATERIALS AND METHODS ASSOCIATED WITH THE SAME	7,339,205	03/04/2008
III-NITRIDE MATERIAL STRUCTURES INCLUDING SILICON SUBSTRATES	7,247,889	07/24/2007
GALLIUM NITRIDE MATERIAL DEVICES AND METHODS OF FORMING THE SAME	7,233,028	06/19/2007
GALLIUM NITRIDE MATERIAL TRANSISTORS AND METHODS ASSOCIATED WITH THE SAME	7,135,720	11/14/2006
GALLIUM NITRIDE MATERIAL DEVICES INCLUDING AN ELECTRODE-DEFINING LAYER AND METHODS OF FORMING THE SAME	7,071,498	07/04/2006

GALLIUM NITRIDE MATERIALS INCLUDING THERMALLY CONDUCTIVE REGIONS	6,956,250	10/18/2005
GALLIUM NITRIDE MATERIALS AND METHODS	6,649,287	11/18/2003
GALLIUM NITRIDE MATERIALS AND METHODS	6,617,060	09/09/2003
GALLIUM NITRIDE MATERIAL DEVICES AND METHODS INCLUDING BACKSIDE VIAS	6,611,002	08/26/2003
GALLIUM NITRIDE MATERIAL TRANSISTORS AND METHODS ASSOCIATED WITH THE SAME	12/508,871	07/24/2009
GALLIUM NITRIDE MATERIAL DEVICES INCLUDING CONDUCTIVE REGIONS AND METHODS ASSOCIATED WITH THE SAME	12/508,891	07/24/2009
GALLIUM NITRIDE MATERIALS AND METHODS	12/343,616	12/24/2008
GALLIUM NITRIDE MATERIAL PROCESSING AND RELATED DEVICE STRUCTURES	12/143,727	06/20/2008
PACKAGED GALLIUM NITRIDE MATERIAL TRANSISTORS AND METHODS ASSOCIATED WITH THE SAME	12/132,985	06/04/2008
EXTERNALLY CONFIGURABLE INTEGRATED CIRCUITS	12/110,816	04/28/2008
GALLIUM NITRIDE MATERIAL DEVICES INCLUDING DIAMOND REGIONS AND METHODS ASSOCIATED WITH THE SAME	12/025,976	02/05/2008
GALLIUM NITRIDE MATERIAL STRUCTURES INCLUDING SUBSTRATES AND METHODS ASSOCIATED WITH THE SAME	12/024,313	02/01/2008
SEMICONDUCTOR DEVICE-BASED SENSORS AND METHODS ASSOCIATED WITH THE SAME	12/023,500	01/31/2008

GALLIUM NITRIDE MATERIALS AND METHODS ASSOCIATED WITH THE SAME	12/023,480	01/31/2008
GALLIUM NITRIDE MATERIALS AND METHODS ASSOCIATED WITH THE SAME	12/023,451	01/31/2008
GALLIUM NITRIDE MATERIAL DEVICES AND METHODS OF FORMING THE SAME	11/762,985	06/14/2007
GALLIUM NITRIDE MATERIAL DEVICES AND ASSOCIATED METHODS	11/607,129	11/30/2006
GALLIUM NITRIDE MATERIAL DEVICES INCLUDING AN ELECTRODE-DEFINING LAYER AND METHODS OF FORMING THE SAME	11/477,834	06/29/2006
GALLIUM NITRIDE MATERIAL TRANSISTORS AND METHODS FOR WIDEBAND APPLICATIONS	11/543,010	10/04/2006
GALLIUM NITRIDE MATERIAL-BASED MONOLITHIC MICROWAVE INTEGRATED CIRCUITS	11/261,942	10/28/2005
GALLIUM NITRIDE MATERIALS INCLUDING THERMALLY CONDUCTIVE REGIONS	11/050,598	02/03/2005
III-NITRIDE MATERIALS INCLUDING LOW DISLOCATION DENSITIES AND METHODS ASSOCIATED WITH THE SAME	10/886,506	07/07/2004
GALLIUM NITRIDE MATERIAL STRUCTURES INCLUDING ISOLATION REGIONS AND METHODS	10/879,695	06/28/2004
GALLIUM NITRIDE MATERIALS AND METHODS	10/675,798	09/30/2003
SEMICONDUCTOR STRUCTURES INCLUDING A GALLIUM NITRIDE MATERIAL COMPONENT AND A SILICON GERMANIUM COMPONENT	10/047,455	01/15/2002
GALLIUM NITRIDE MATERIAL PROCESSING AND RELATED DEVICE STRUCTURES	PCT/US2009/002663	04/29/2009

EXHIBIT C

Trademarks

<u>Description</u>	<u>Registration/ Application Number</u>	<u>Registration/ Application Date</u>
SIGANTIC (Registered)	3,091,510	05/09/2006
NITRONEX (Registered)	2,967,342	07/12/2005
SIGANTIC (Registered)	2,952,096	05/17/2005
N (Registered)	2,949,681	05/10/2005
NITRONEX (Registered)	2,925,552	02/08/2005
IT'S WATTS IN THE PACKAGE (Pending)	77/447,606	04/14/2008
SIGANTIC (Abandoned)	76/211,995	02/16/2001
PENDEO (Abandoned)	75/844,687	11/09/1999
PENDEOEPITAXY (Abandoned)	75/845,791	11/09/1999
NITRONEX CORPORATION (Abandoned)	75/658,492	03/11/1999

EXHIBIT D

Mask Works

<u>Description</u>	Registration/ Application <u>Number</u>	Registration/ Application <u>Date</u>
None		